

FIG. 2

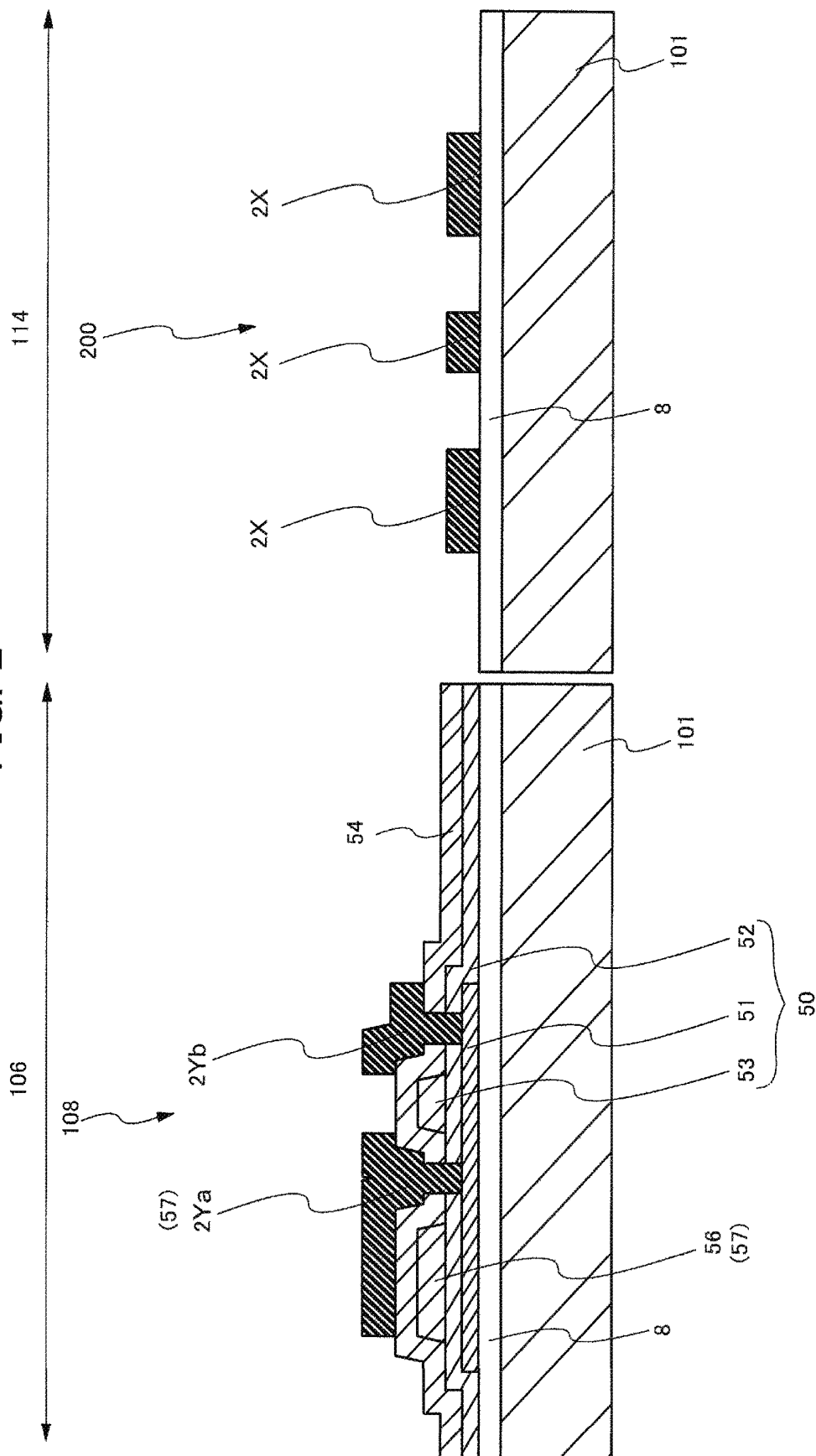


FIG. 3

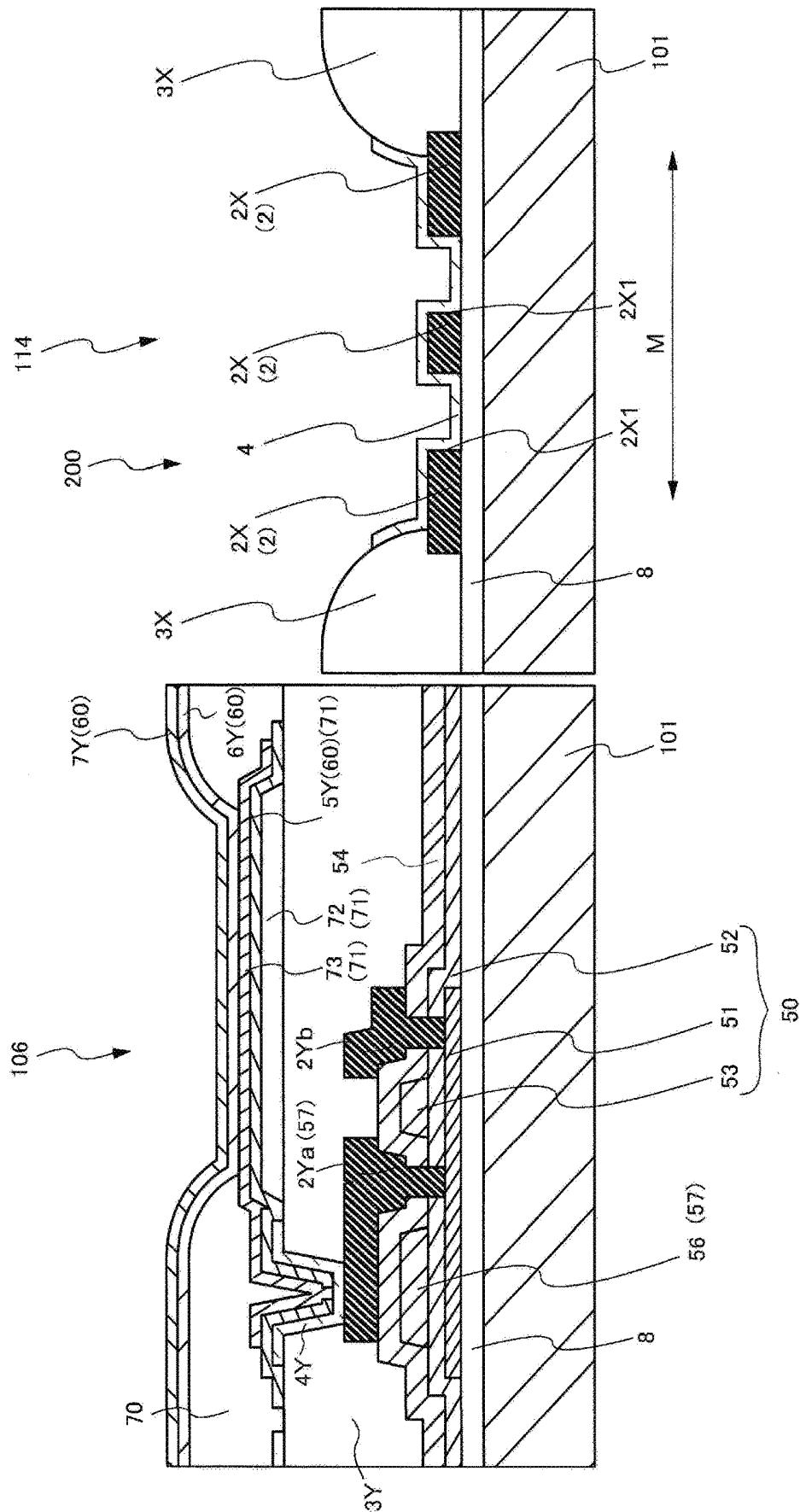


FIG. 4

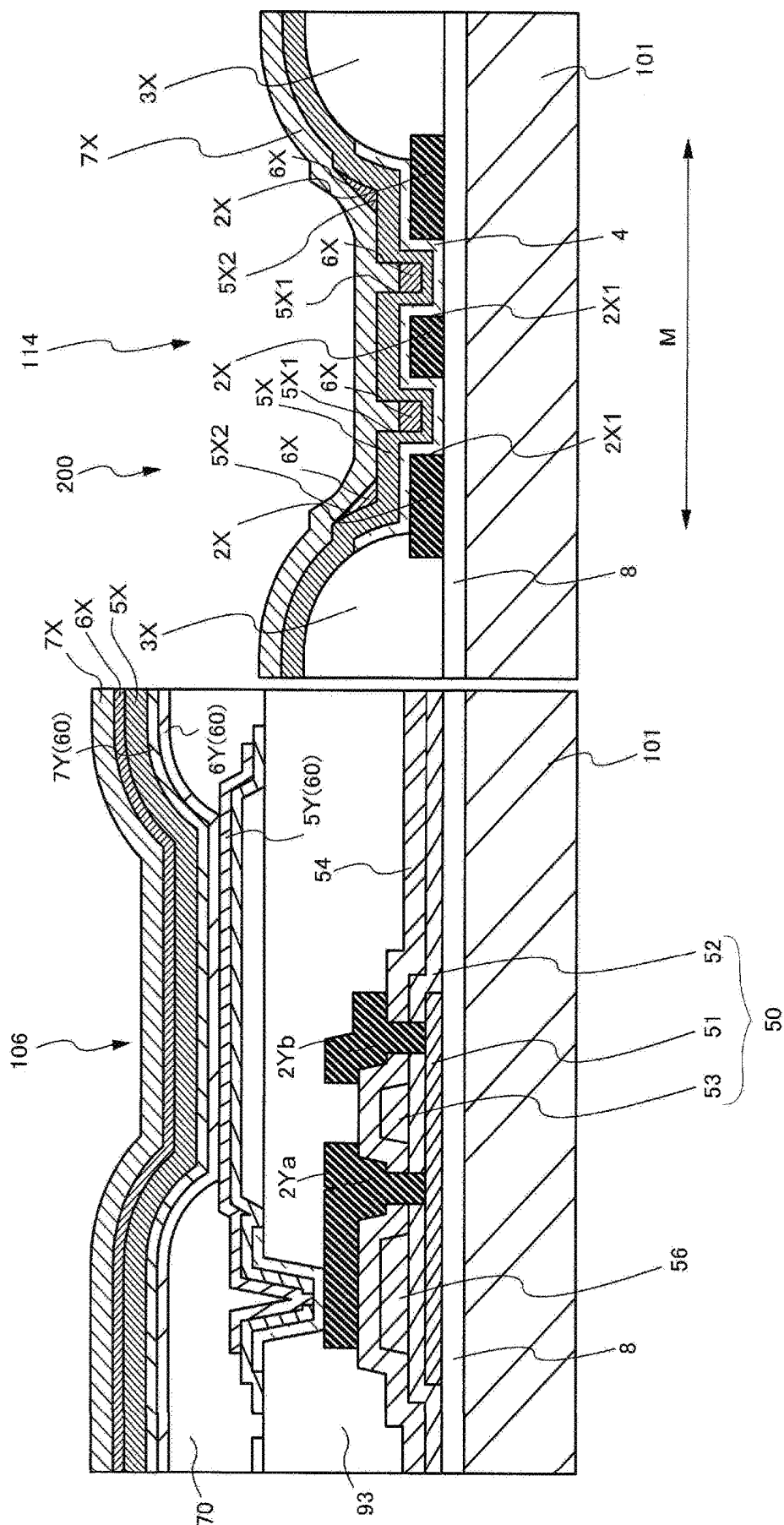


FIG. 5

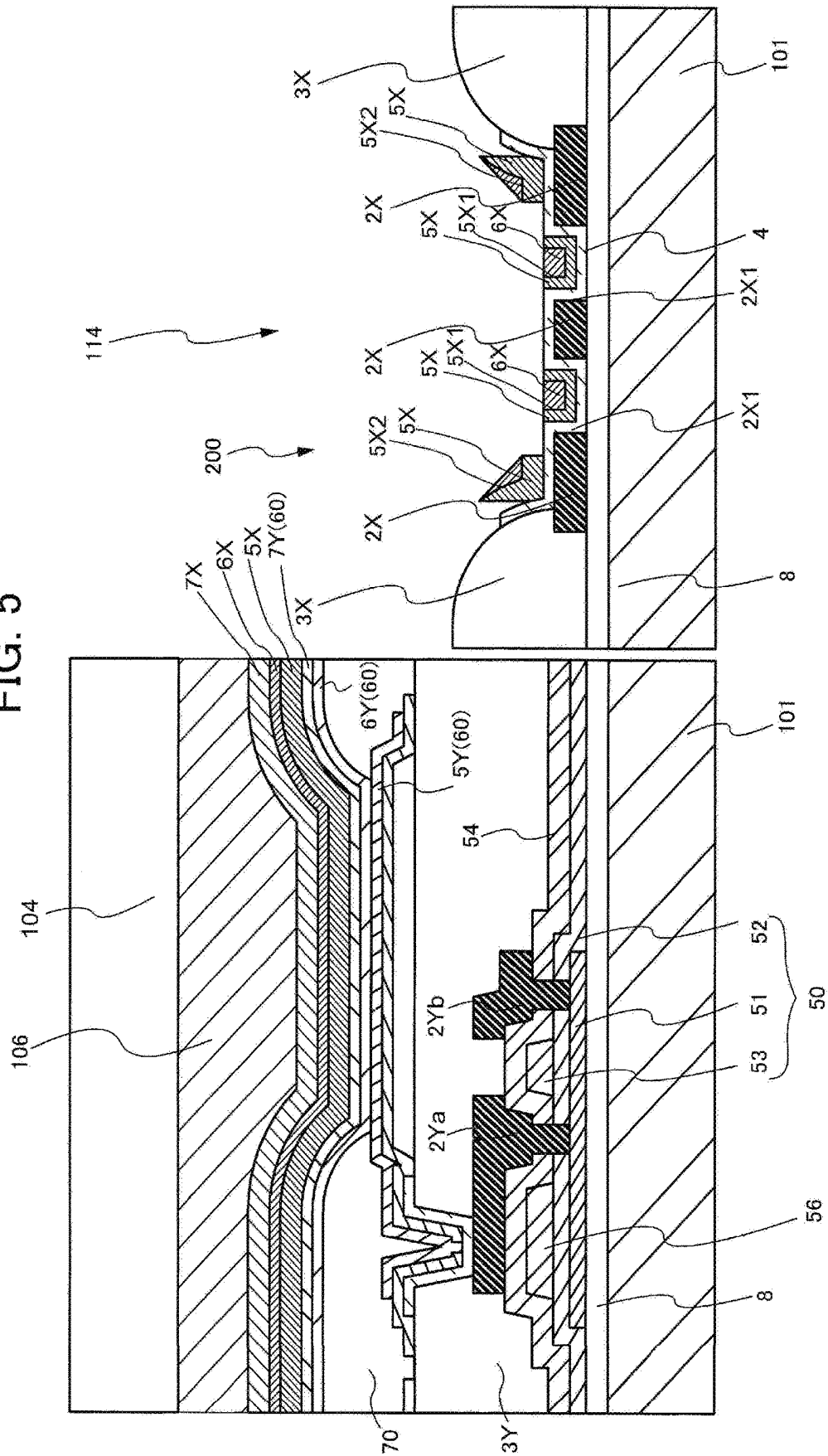


FIG. 6

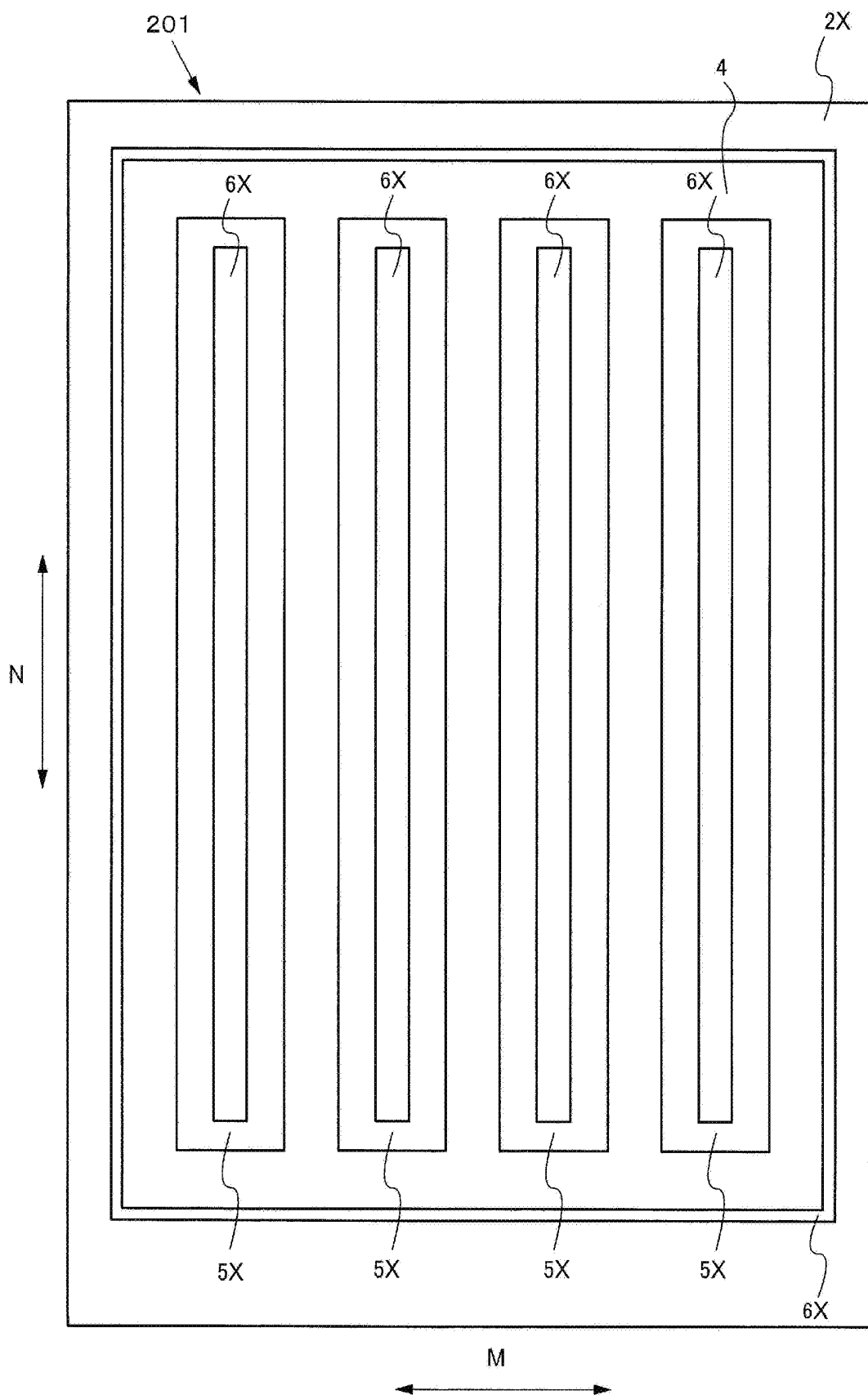


FIG. 7

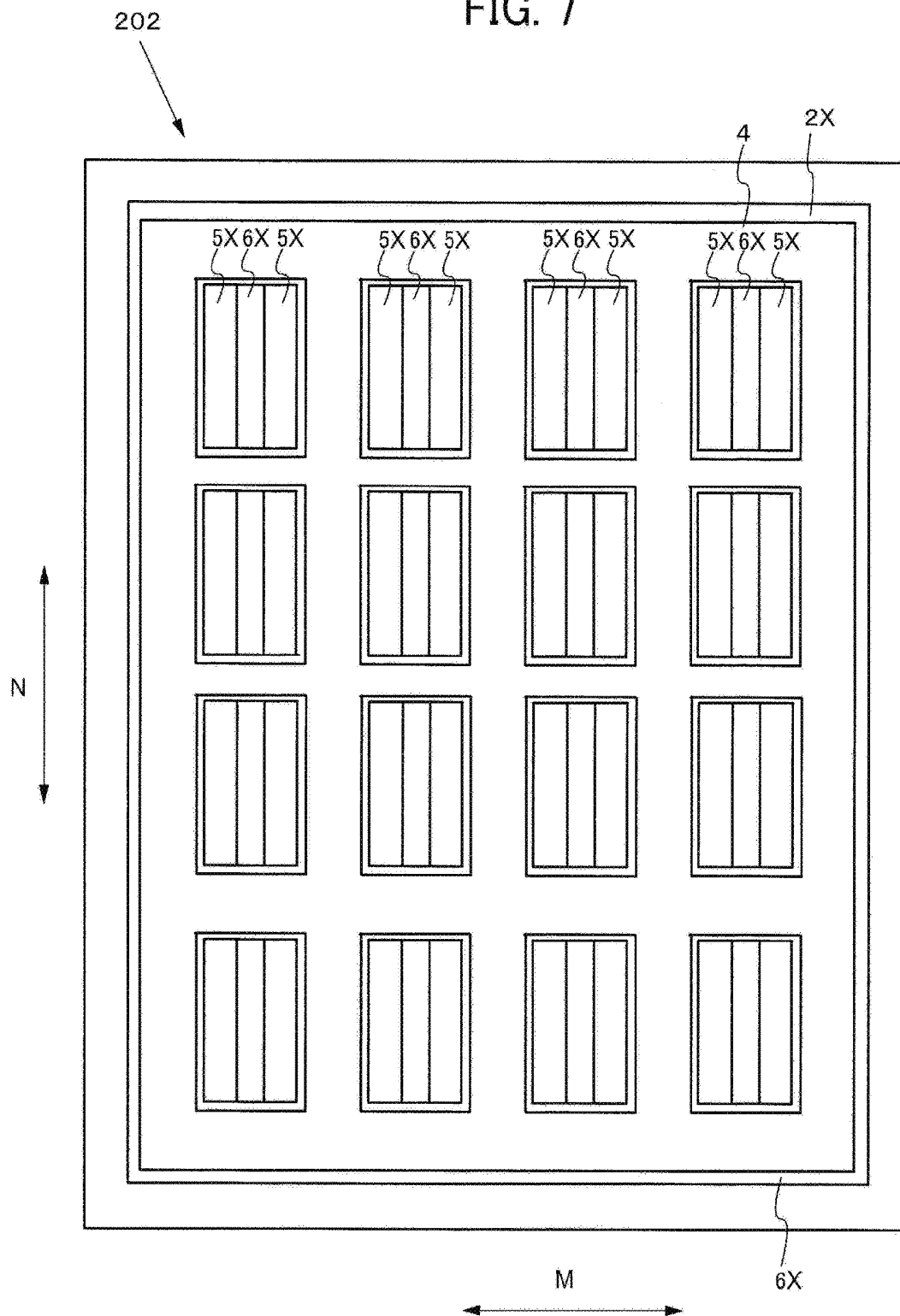


FIG. 8

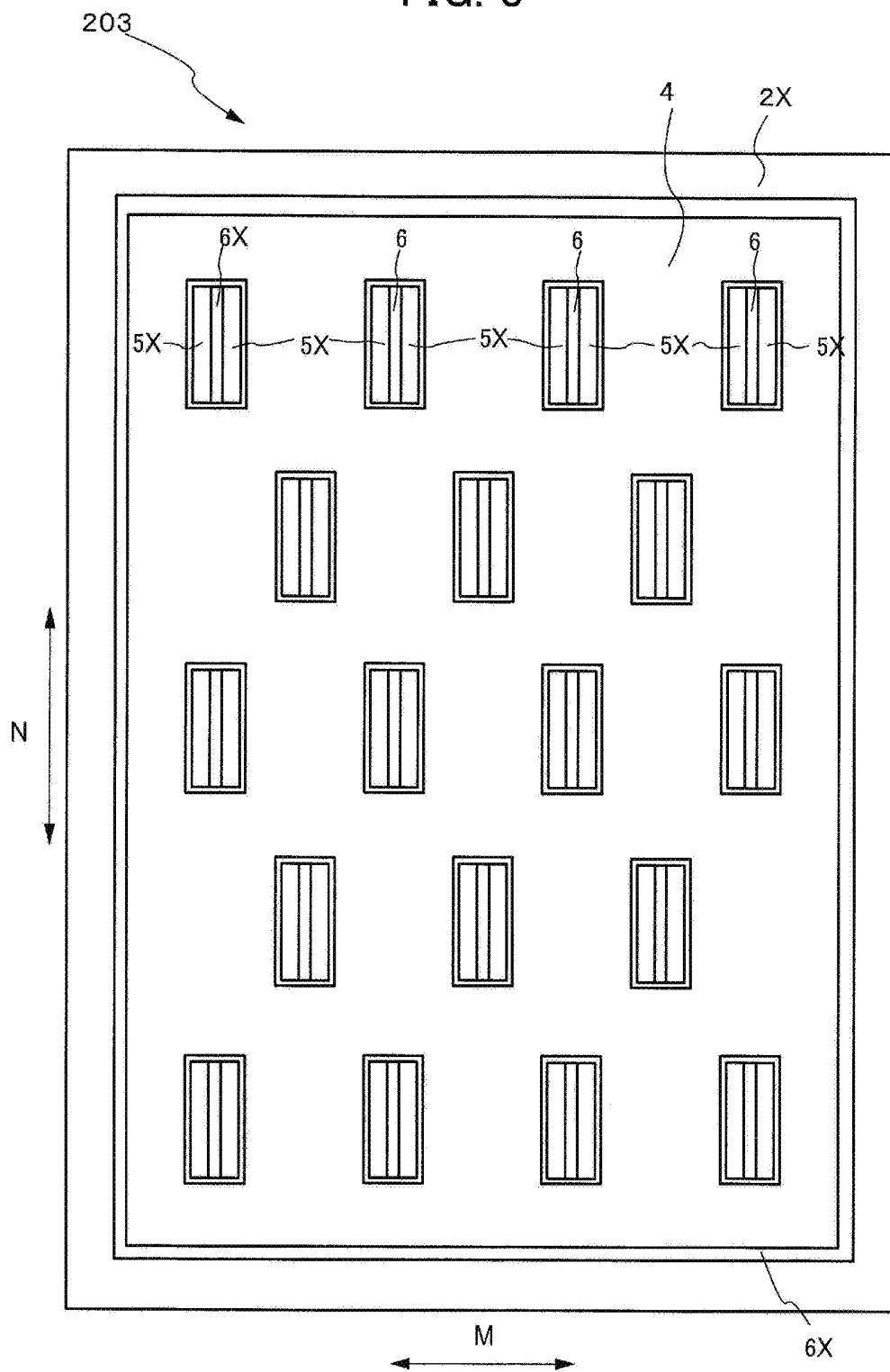
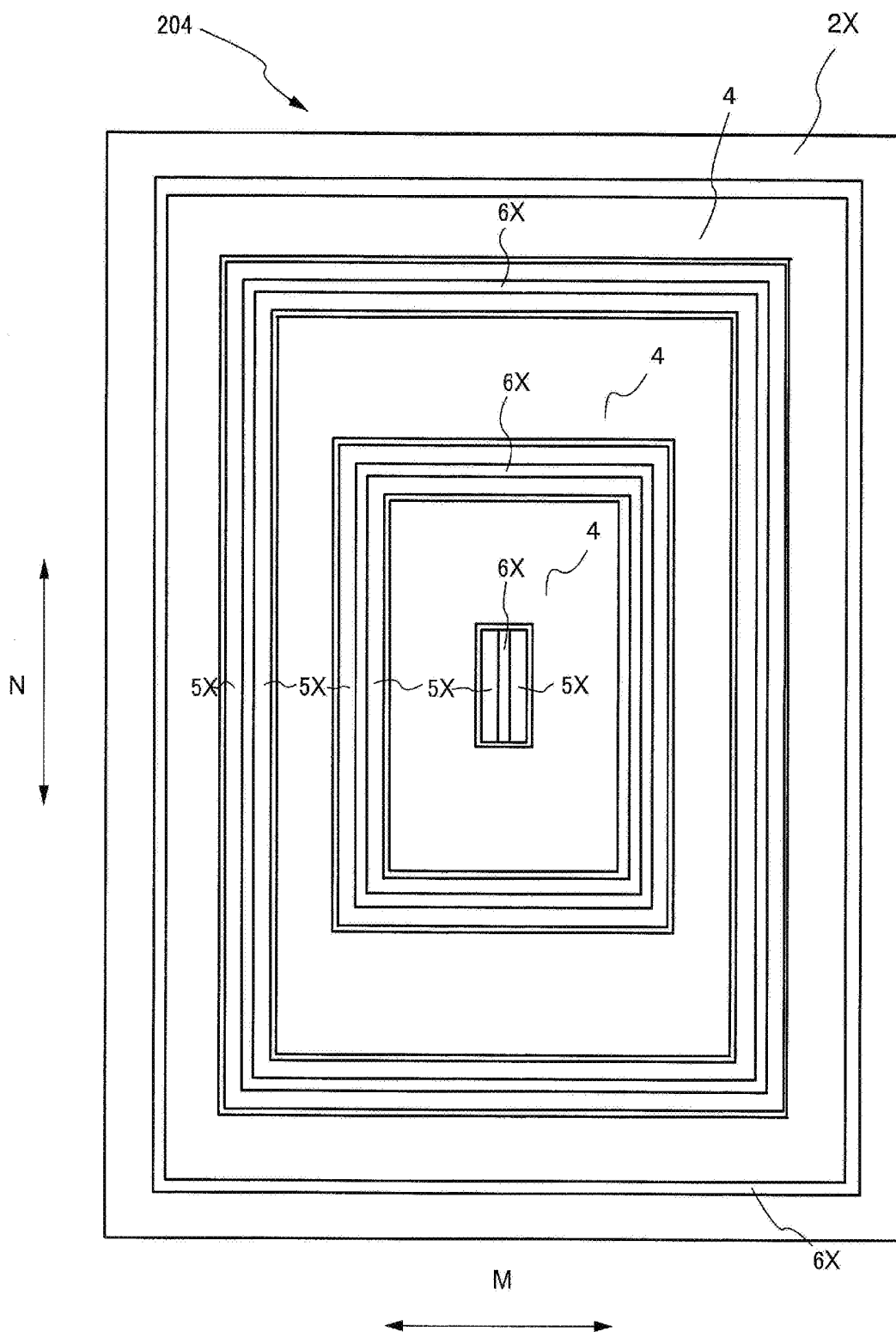
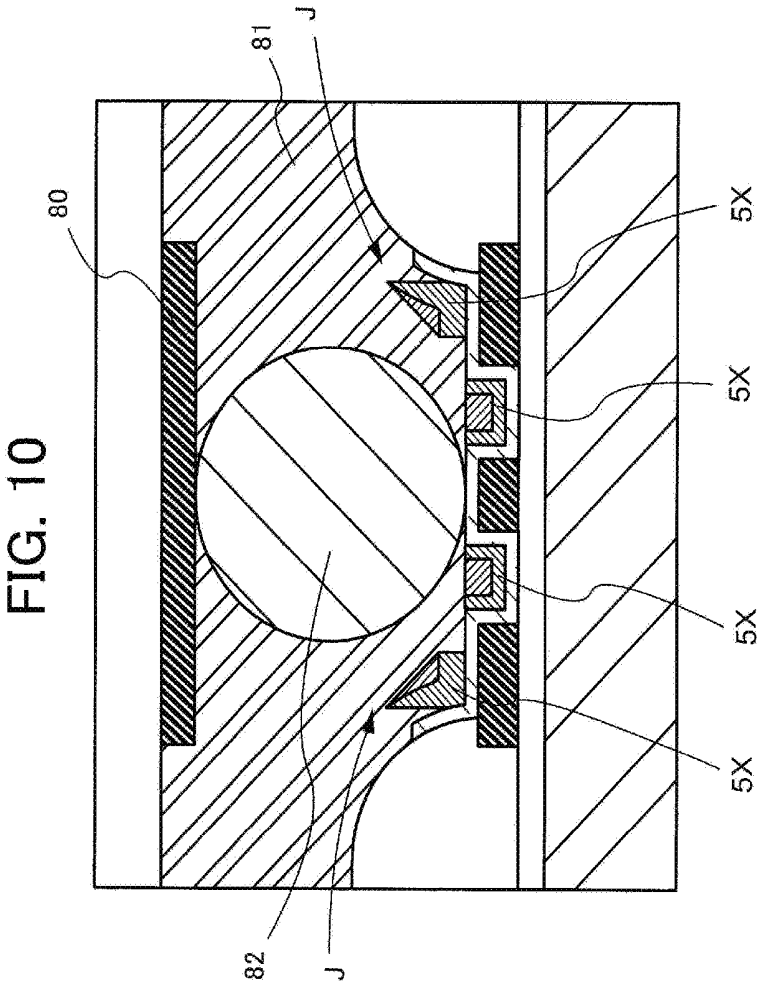


FIG. 9





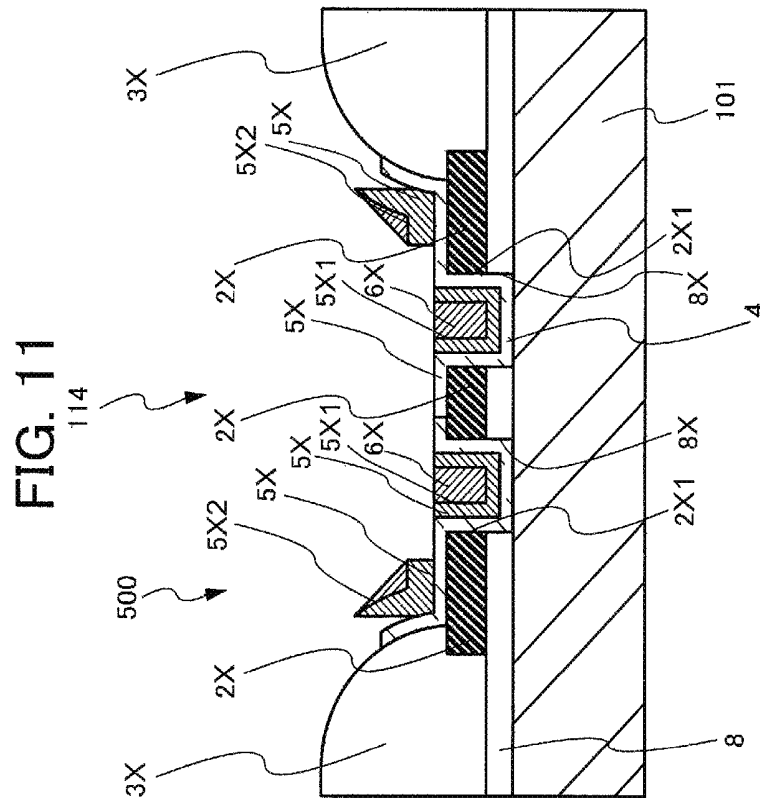
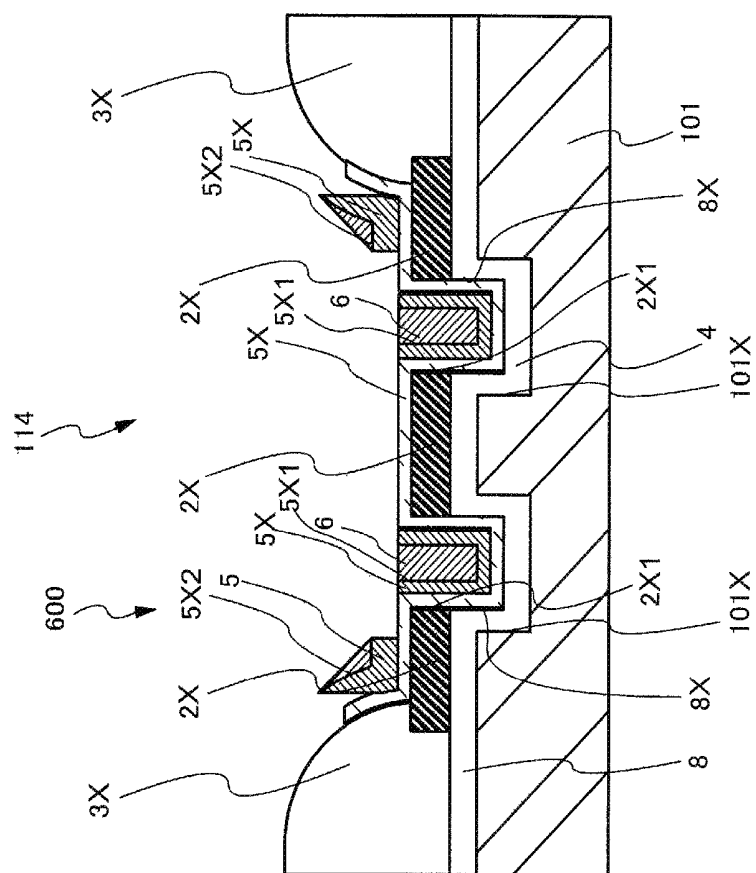


FIG. 12



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MANUFACTURING METHOD OF DISPLAY DEVICE AND DISPLAY DEVICE

CROSS REFERENCE TO RELATED APPLICATIONS

This application is based upon and claims the benefit of priority from the prior Japanese Patent Application No. 2016-32861, filed on Feb. 24, 2016, the entire contents of which are incorporated herein by reference.

FIELD

The present invention relates to a manufacturing method of a display device and to a display device.

BACKGROUND

Japanese Laid-Open Patent Publication No. 2015-69857 discloses a display device including pixels each including a light emitting element formed of an organic electroluminescence (hereinafter, referred to as "organic EL") material. In this display device, a protective layer covering an organic EL layer is used as a sealing film. The protective layer includes a plurality of insulating layers (three layers of inorganic insulating layer/organic insulating layer/inorganic insulating layer) provided in a stacked manner.

Among the plurality of insulating layers, which are provided on a top surface of the organic EL layer, the inorganic layers are formed by sputtering and the organic layer is formed by application. Therefore, the plurality of insulating layers are provided in a pixel region (display region) and also extend to a terminal region (non-display region) of the display device. For this reason, on the region of each of connection terminals in the terminal region, the insulating layers need to be in a removable state and the connection terminals need to be in a conductive state.

The insulating layers may be removed from the terminal region by dry etching or wet etching. However, in order to remove the insulating layers including the inorganic insulating layer/organic insulating layer/inorganic insulating layer provided in a stacked manner, etching conditions suitable to the respective insulating layers need to be set. This involves problems that, for example, the manufacturing process is complicated, the margin is reduced, the tact time is increased, and in some cases, a plurality of processing chambers may be needed.

SUMMARY

According to an embodiment of the present invention, there is provided a manufacturing method of a display device including a pixel region including a plurality of pixels each including a light emitting element and a terminal region provided outside the pixel region and including connection terminals; the method comprising: forming a recessed portion in a part of a top surface of each of the connection terminals; forming a first inorganic insulating layer, an organic insulating layer, and a second inorganic insulating layer sequentially in the pixel region and continuously in the terminal region; and etching the first inorganic insulating layer and the second inorganic insulating layer in an area where the first inorganic insulating layer and the second inorganic insulating layer are stacked directly, the area being on the top surface except the recessed portion.

According to an embodiment of the present invention, there is provided a display device, comprising: a substrate;

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a pixel region including a plurality of pixels each including a light emitting element; a terminal region provided outside the pixel region, the terminal region including connection terminals; and a plurality of insulating layers provided from the pixel region to the terminal region continuously; wherein: the connection terminals each include a recessed portion in a part of a top surface thereof, the recessed portion having a dent recessed toward the substrate; in the pixel region, the plurality of insulating layers include a first inorganic insulating layer, an organic insulating layer provided on the first inorganic insulating layer, and a second inorganic insulating layer provided on the organic insulating layer; the top surface is exposed by the plurality of insulating layers; and the first inorganic insulating layer and the second inorganic insulating layer are provided in the dent of the recessed portion.

BRIEF DESCRIPTION OF DRAWINGS

FIG. 1 is a perspective view showing a structure of a display device to which a manufacturing method in an embodiment according to the present invention is applicable;

FIG. 2 is a cross-sectional view showing a state where on a first substrate, a pixel is partially formed in a pixel region and a connection terminal is partially formed in a terminal region;

FIG. 3 is a cross-sectional view showing a state where a light emitting element, a third conductive layer and a second conductive layer are formed;

FIG. 4 is a cross-sectional view showing a state where a pixel electrode, an organic insulating layer and a counter electrode are formed in the pixel region, and a protective layer including a stack of a first inorganic insulating layer, an organic insulating layer and a second inorganic insulating layer is formed on the connection terminal;

FIG. 5 is a cross-sectional view showing a state where a second substrate is formed in the pixel region;

FIG. 6 is a plan view showing a structure of a connection terminal in modification 1 of embodiment 1;

FIG. 7 is a plan view showing a structure of a connection terminal in modification 2 of embodiment 1;

FIG. 8 is a plan view showing a structure of a connection terminal in modification 3 of embodiment 1;

FIG. 9 is a plan view showing a structure of a connection terminal in modification 4 of embodiment 1;

FIG. 10 is a cross-sectional view showing a state where an FPC is formed in the terminal region;

FIG. 11 is a cross-sectional view showing a step of forming layers of a connection terminal in embodiment 2 according to the present invention; and

FIG. 12 is a cross-sectional view showing a step of forming layers of a connection terminal in embodiment 3 according to the present invention.

DESCRIPTION OF EMBODIMENTS

Hereinafter, embodiments of the present invention will be described with reference to the drawings and the like. The present invention may be carried out in many different embodiments, and should not be construed as being limited to any of the following embodiments. In the drawings, components may be shown schematically regarding the width, thickness, shape and the like, instead of being shown in accordance with the actual sizes, for the sake of clear illustration. The drawings are merely exemplary and do not limit the interpretations of the present invention in any way.

In the specification and the drawings, components that are substantially the same as those shown in a previous drawing(s) bear the identical reference signs thereto, and detailed descriptions thereof may be omitted. The following embodiments have an object of simplifying the step of exposing a conductive surface in a region for each of connection terminals of the display device.

In this specification, an expression that a component or area is "on" another component or area encompasses a case where such a component or area is in contact with the another component or area and also a case where such a component or area is above or below the another component or area, namely, a case where still another component or area is provided between such a component or area and the another component or area, unless otherwise specified.

Embodiment 1

FIG. 1 is a perspective view showing a structure of a display device **100** in embodiment 1. The display device **100** includes a first substrate **101** (may be simply referred to as a "substrate") and a display region **106** provided thereon. The display region **106** includes an array of a plurality of pixels **108**, each of which includes a light emitting element. The light emitting element includes a layer containing a light emitting material (light emitting layer), which is provided between a pair of electrodes. Herein, the light emitting element is, for example, an organic EL element including a layer containing an organic electroluminescence material as the light emitting material. A second substrate **104** acting as a sealing member is provided on a top surface of the pixel region **106**.

The second substrate **104** is secured to the first substrate **101** by a sealing member **110** enclosing the pixel region **106**. The display region **106** formed on the first substrate **101** is sealed by the second substrate **104** acting as a sealing member and the sealing member **110** so as not to be exposed to the air. Such a sealing structure suppresses light emitting elements provided in the pixels **108** from being deteriorated. The light emitting elements are also sealed by a protecting layer including insulating layers described below (see FIG. 4).

The first substrate **101** has a terminal region **114** provided thereon along an end thereof. The terminal region **114** is located outside the second substrate **104**. The terminal region **114** includes a plurality of connection terminals **200**, which are provided outside the pixel region **106** and are each connectable with a wiring board such as a flexible printed circuit board (hereinafter, also referred to as the "FPC **80**" (see FIG. 10)) or the like.

The connection terminals **200** are each connectable with the wiring board, which connects a device that outputs a video signal, a power supply or the like with a display panel. A contact of the connection terminal **200** with the wiring board is exposed outside. The first substrate **101** has a driver IC **112** provided thereon, which outputs a video signal input from the terminal region **114** to the pixel region **106**.

Hereinafter, a manufacturing method of the display device **100** in an embodiment according to the present invention will be described. FIG. 2 shows a state where on the first substrate **101**, a part of the pixel **108** is formed in the pixel region **106**, and the connection terminal **200** is partially formed in the terminal region **114**. The terminal region **114** of FIG. 2 is equivalent to the cross section along the A-B line of FIG. 1 (this also applies to FIG. 3 through FIG. 5). The

pixel region **106** of FIG. 2 is equivalent to the cross section along the C-D line of FIG. 1 (this also applies to FIG. 3 through FIG. 5).

The pixel **108** is formed to include a transistor **50** and a light emitting element **60** (see FIG. 3). The transistor **50** includes a semiconductor layer **51**, a gate insulating layer **52** and a gate electrode **53**, which are formed on an underlying insulating layer **8**.

In source/drain regions of the transistor **50**, source/drain electrodes **2Ya** and **2Yb** are formed while having a first interlayer insulating layer **54** held therebetween. A second interlayer insulating layer **3Y** is formed to embed the source/drain electrodes **2Ya** and **2Yb**.

The source/drain electrode **2Ya** connected with the transistor **50** and a first capacitance electrode **56** formed on the gate insulating layer **52** form a first capacitance element **57**. The first interlayer insulating layer **54** provided between the first capacitance electrode **56** and the source/drain electrode **2Ya** also acts as a dielectric layer of the first capacitance element **57**.

FIG. 3 is a cross-sectional view showing a state where the light emitting element **60**, a third conductive layer **4Y** and a second conductive layer **4** are formed. The light emitting element **60** includes a stack of a pixel electrode **5Y**, an organic insulating layer **6Y** and a counter electrode **7Y**. The pixel electrode **5Y** is enclosed by a bank layer **70**.

The second interlayer insulating layer **3Y** is formed between the pixel electrode **5Y** and the source/drain electrodes **2Ya** and **2Yb**. The second interlayer insulating layer **3Y** is formed of an organic insulating material. Since the second interlayer insulating layer **3Y** is formed of an organic insulating material, a surface on which the light emitting element **60** is to be formed is flattened. The organic insulating material is, for example, a material containing an acrylic resin or the like.

In the example shown in FIG. 3, a second capacitance element **71** is provided so as to overlap the light emitting element **60**. The second capacitance element **71** includes a second capacitance electrode **72**, a third insulating layer **73** and the pixel electrode **5Y**.

The light emitting element **60** and the transistor **50** are connected with each other via a contact hole formed in the second interlayer insulating layer **3Y**. In the example shown in FIG. 3, the third conductive layer **4Y** is provided between the pixel electrode **5Y** and the source/drain electrode **2Ya**. The third conductive layer **4Y** is formed of, for example, a conductive metal oxide such as ITO or the like.

A first conductive layer **2X** is formed of aluminum or an aluminum alloy having a low resistivity. A conductive metal oxide layer harder than aluminum is provided on a surface of the first conductive layer **2X** to protect the first conductive layer **2X**. Hereinafter, the connection terminal **200** will be specifically described.

The connection terminal **200** is provided on the first substrate **101** (substrate material). The first substrate **101** is formed of a resin or glass. On the first substrate **101**, the underlying insulating layer **8** is formed. The underlying insulating layer **8** is formed of, for example, silicon oxide, silicon nitride or the like.

On the underlying insulating layer **8**, the first conductive layer **2X** is formed. The first conductive layer **2X** is formed of, for example, an aluminum-containing compound (aluminum-based material) or the like.

In the terminal region **114**, the connection terminal **200** includes the first conductive layer **2X** and the second conductive layer **4** described below. The surface of the first conductive layer **2X** (a part of a top surface of the connec-

tion terminal **200**) has recessed portions **2X1** (recessed area). The recessed portions **2X1** each include a dent that is recessed toward the first substrate **101**. The recessed portions **2X1** may be openings running throughout the first conductive layer **2X** or may be formed as a result of a part of the first conductive layers **2X** being thinned. In the latter case, the recessed portions **2X1** each have a bottom surface. It may be expressed that in a region for the connection terminal **200**, the first conductive layer **2X** is partially removed (the connection terminal **200** is partially removed) to form the recessed portions **2X1**.

The second conductive layer **4** is provided on the first conductive layer **2X** and in the recessed portions **2X1**. After the first conductive layer **2X** is formed but before the second conductive layer **4** is formed, a flattening film **3X** is formed on two ends, in a width direction **M**, of the first conductive layer **2X**. More specifically, the flattening film **3X** is formed on the two ends, in the width direction **M**, of the first conductive layer **2X** in the region for the connection terminal **200**.

The second conductive layer **4** is formed on each part of the flattening film **3X** on the side closer to the center in the width direction **M**, on the surface of the first conductive layer **2X**, in the recessed portions **2X1**, and on a surface of the underlying insulating layer **8** acting as the bottom surface of the recessed portions **2X1**. The second conductive layer **4** is formed of a conductive metal oxide such as, for example, indium tin oxide (ITO) or the like.

The first conductive layer **2X**, for example, forms the same layer with the source/drain electrodes **2Ya** and **2Yb** in the pixel **108** (see FIG. 1). Alternatively, the first conductive layer **2X** may form the same layer with the gate electrode **53**. In either case, the first conductive layer **2X** is once embedded by the second interlayer insulating layer **3Y** and the flattening film **3X**, which are formed on the entirety over the first substrate **101**.

However, after the second interlayer insulating layer **3Y** is formed, a contact hole needs to be formed in the second interlayer insulating layer **3Y** in order to connect the pixel electrode **5Y** of the light emitting element **60** and the transistor **50** with each other. The step of forming the contact hole is the step of removing a part of the second interlayer insulating layer **3Y**.

In the same step as the removal of the part of the second interlayer insulating layer **3Y** in the pixel region **106**, the flattening film **3X** is removed in the terminal region **114** so as to expose the surface of the first conductive layer **2X**.

In this case, the flattening film **3X** in the terminal region **114** may be entirely removed. Alternatively, as shown in FIG. 3, the flattening film **3X** may be partially removed and thus partially left so as to enclose the first conductive layer **2X**. In the case where the flattening film **3X** is left so as to enclose the first conductive layer **2X**, the coverage of steps of the second conductive layer **4** is improved. This will be described more specifically. The top surface and side surfaces of the first conductive layer **2X** are covered with the second conductive layer **4**. However, the second conductive layer **4** does not sufficiently cover the stepped portions (side surfaces) of the first conductive layer **2X**. The flattening film **3X** left so as to enclose the conductive layer **2X** alleviates this inconvenience. The second interlayer insulating layer **3Y** and the flattening film **3X** may be formed of a photo-sensitive resin.

FIG. 4 shows a state where the pixel electrode **5Y**, the organic insulating layer **6Y** and the counter electrode **7Y** are formed in the pixel region **106**, and then a protective layer including a stack of a first inorganic insulating layer **5X**, an

organic insulating layer **6X** and a second inorganic insulating layer **7X** is formed in the pixel region **106** and the terminal region **114**. Among the layers of the protective layer, the inorganic insulating layers **5X** and **7X** are formed by sputtering, and the organic insulating layer **6X** is formed by application. Therefore, the protective layer is formed on substantially the entirety over the first substrate **101**. As a result, in the terminal region **114**, the organic insulating layer **6X** is concentrated in the recessed portions **2X1**. In the pixel region **106**, the protective layer including the stack of the first inorganic insulating layer **5X**, the organic insulating layer **6X** and the second inorganic insulating layer **7X** is located on the counter electrode **7Y**, and protects and seals the light emitting element **60**. Specifically, the protective layer is formed as follows.

As shown in FIG. 4, the first inorganic insulating layer **5X** is formed in the pixel region **106** and continuously in the terminal region **114**. Specifically in the terminal region **114**, the first inorganic insulating layer **5X** is formed on a stack of the first conductive layer **2X** and the second conductive layer **4** and on the flattening film **3X**. A surface of the first inorganic insulating layer **5X** is recessed to form recessed portions **5X1** and stepped portions **5X2**.

Then, in the pixel region **106** and continuously in the terminal region **114**, the organic insulating layer **6X** is formed. Specifically in the terminal region **114**, the organic insulating layer **6X** is formed on the first inorganic insulating layer **5X**. The organic insulating layer **6X** is formed by applying and baking a flowable resin composition.

By contrast, the resin composition applied to the region for the connection terminal **200** flows toward the recessed portions **2X1** of the first conductive layer **2X** but does not stay around the recessed portions **2X1**. Therefore, in the terminal region **114**, the organic insulating layer **6X** is formed based on the shape of the recessed portions **2X1**. Namely, the resin composition is concentrated in the recessed portions **5X1** and the stepped portions **5X2** of the first inorganic insulating layer **5X**. The organic insulating layer **6X** is formed of an insulating resin material such as an acrylic resin, polyimide or the like.

In the terminal region **114**, the second inorganic insulating layer **7X** is formed on the first inorganic insulating layer **5X** having the organic insulating layer **6X** formed therein. In this manner, the plurality of insulating layers, specifically, the first inorganic insulating layer **5X**, the organic insulating layer **6X** and the second inorganic insulating layer **7X**, are formed.

In the region for the connection terminal **200**, the first inorganic insulating layer **5X** and the second inorganic insulating layer **7X** are adjacent to each other in a stacked state in an up-down direction in an area except for the recessed portions **2X1** in the width direction **M**. In this example, the first inorganic insulating layer **5X** and the second inorganic insulating layer **7X** are formed of the same material as each other. Therefore, the first inorganic insulating layer **5X** and the second inorganic insulating layer **7X** are etched in the same step. In this case, as compared with the case where the first inorganic insulating layer **5X**, the organic insulating layer **6X** and the second inorganic insulating layer **7X** provided in a stacked manner are etched, the number of etching steps is decreased (from three steps to one step).

In the case where the first inorganic insulating layer **5X** and the second inorganic insulating layer **7X** are formed of different materials from each other, the second inorganic insulating layer **7X** is etched and then the first inorganic insulating layer **5X** is etched. Even in this case, as compared

with the case where the first inorganic insulating layer 5X, the organic insulating layer 6X and the second inorganic insulating layer 7X provided in a stacked manner are etched, the number of etching steps is decreased (from three steps to two steps).

FIG. 5 shows a state where the second substrate 104 shown in FIG. 1 is provided in the pixel region 106. In the terminal region 114, the first inorganic insulating layer 5X and the second inorganic insulating layer 7X are etched after the state of the terminal region 114 become as shown in FIG. 4.

In each of the recessed portions 2X1, the second conductive layer 4 and the first inorganic insulating layer 5X are formed along the shape of the recessed portion 2X1, and the organic insulating layer 6X (organic resin layer) is formed in the recessed portion 5X1 of the first inorganic insulating layer 5X. The organic insulating layer 6X is formed of, for example, an acrylic resin.

It is preferable that as seen from a direction perpendicular to the directions in which the first substrate 101 expands, the second conductive layer 4 has an area size that is 50% or more of the area size of the first conductive layer 2X.

In this manner, the plurality of insulating layers including the first inorganic insulating layer 5X, the organic insulating layer 6X and the second inorganic insulating layer 7X are formed in the pixel region 106. In the same step, in the region for the connection terminal 200, the second conductive layer 4 is exposed from the plurality of insulating layers, and the first inorganic insulating layer 5X and the organic insulating layer 6X are provided in the recessed portions 2X1. Therefore, the plurality of insulating layers are formed from the pixel region 106 to the terminal region 114.

FIG. 6 is a plan view of a connection terminal 201 in modification 1 of embodiment 1. The connection terminal 201 includes a plurality of unit areas each including the first inorganic insulating layer 5X and the organic insulating layer 6X both extending in a length direction N. The first inorganic insulating layer 5X and the organic insulating layer 6X are provided on the first conductive layer 2X. Such unit areas are provided in a matrix of 1 (length direction N)×4 (width direction M).

FIG. 7 is a plan view of a connection terminal 202 in modification 2 of embodiment 1. The connection terminal 202 includes a plurality of unit areas each including the first inorganic insulating layer 5X and the organic insulating layer 6X both extending in the length direction N. The first inorganic insulating layer 5X and the organic insulating layer 6X are provided on the first conductive layer 2X. Such unit areas are provided in a matrix of 4 (length direction N)×4 (width direction M).

FIG. 8 is a plan view of a connection terminal 203 in modification 3 of embodiment 1. The connection terminal 203 includes a plurality of unit areas each including the first inorganic insulating layer 5X and the organic insulating layer 6X both extending in the length direction N. The first inorganic insulating layer 5X and the organic insulating layer 6X are provided on the first conductive layer 2X. Such unit areas are arranged in five rows; namely, five such unit areas are provided in the length direction N. Regarding the width direction M, in first, third and fifth rows, four such unit area are provided, and in the second and fourth rows, three such unit areas are provided. The four unit areas and the three unit areas are provided alternately.

FIG. 9 is a plan view of a connection terminal 204 in modification 4 of embodiment 1. The connection terminal 204 includes a plurality of unit areas each including the first inorganic insulating layer 5X and the organic insulating

layer 6X. The first inorganic insulating layer 5X and the organic insulating layer 6X are provided on the first conductive layer 2X. In the central unit area in FIG. 9, the first inorganic insulating layer 5X and the organic insulating layer 6X extend in the length direction N. In the other unit areas, the first inorganic insulating layer 5X and the organic insulating layer 6X extend in both of the length direction N and the width direction M, namely, in a hole shape or a rectangular frame pattern.

Regarding FIG. 6 through FIG. 9, there is no specific limitation on the number of the recessed portions 2X1. In FIG. 6 through FIG. 9, it is preferable that the area size of the exposed part of the second conductive layer 4 is 50% or more of the area size of the first conductive layer 2X.

FIG. 10 shows a state where the FPC 80 is provided in the terminal region 114. The connection terminal 200 is connected with FPC 80 by, for example, an anisotropic conductive adhesive (ACF) 81. A conductive bead 82 is larger than the first inorganic insulating layer 5X left in areas represented by arrow J. Therefore, even in the case where the first inorganic insulating layer 5X is left in the areas represented by arrow J as shown in FIG. 10, the first inorganic insulating layer 5X does not have any influence, but may rather act as a stopper for the conductive bead 82.

Embodiment 2

Now, with reference to FIG. 11, a structure of a connection terminal 500 in embodiment 2 will be described. FIG. 11 is a cross-sectional view showing a state where etching performed on the insulating layers in the connection terminal 500 is finished. Unlike in the connection terminal 200 in embodiment 1, in the connection terminal 500 in embodiment 2, the underlying insulating layer 8 is partially removed in a region for the connection terminal 500 to form recessed portions. More specifically, the underlying insulating layer 8 and the first conductive layer 2X are formed on the first substrate 101, and then, the recessed portions each including a recessed portion 8X and the recessed portion 2X1 communicated with each other are formed.

Alternatively, the recessed portions may be formed as follows. The recessed portions 8X are formed in the underlying insulating layer 8. Then, the first conductive layer 2X is formed thereon, and the first conductive layer 2X is partially removed to form the recessed portions 2X1.

Embodiment 3

Now, with reference to FIG. 12, a structure of a connection terminal 600 in embodiment 3 will be described. FIG. 12 is a cross-sectional view showing a state where etching performed on the insulating layers in the connection terminal 600 is finished. Unlike in the connection terminal 200 in embodiment 1, in the connection terminal 600 in embodiment 3, the first substrate 101 is partially removed to form recessed portions. More specifically, the first substrate 101 is partially removed to form recessed portions 101X, then the underlying insulating layer 8 and the first conductive layer 2X are formed, and the recessed portions 8X and 2X1 are formed.

Alternatively, the recessed portions may be formed as follows. The underlying insulating layer 8 is formed on the first substrate 101, and then recessed portions each including the recessed portion 101X and the recessed portion 2X1 communicated with each other are formed. Then, the first conductive layer 2X is formed thereon, and the first conductive layer 2X is partially formed to form the recessed

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portions **2X1**. Still alternatively, the recessed portions may be formed as follows. The underlying insulating layer **8** and the first conductive layer **2X** are formed on the first substrate **101**. Then, recessed portions each including the recessed portion **101X**, the recessed portion **8X** and the recessed portion **2X1** are formed.

With any of the methods in embodiments 1 through 3, the organic insulating layer **6X** is concentrated in the first inorganic insulating layer **5X** (more specifically, in the recessed portions **5X1**) formed in the recessed portions **2X1**. Therefore, after the step of forming the plurality of insulating layers (the first inorganic insulating layer **5X**, the organic insulating layer **6X**, and the second inorganic insulating layer **7X**) in a stacked manner on the first conductive layer **2X**, which is formed on the first substrate **101**, the plurality of insulating layers on the first conductive layer **2X** may be removed more easily than by a conventional method.

As a result, for example, in each of the embodiments, the manufacturing process of the connection terminals is simplified, the time for the manufacturing is shortened, and the stability is improved in the manufacturing. In addition, the first conductive layer **2X** having the recessed portions **2X1** allows the IC or FPC **80** to be connected by an ACF with more certainty than a flat first conductive layer. Thus, the reliability of the product, for example, the display device **100**, is improved.

What is claimed is:

1. A display device, comprising:

a substrate;

a pixel region including a plurality of pixels each including a light emitting element;

a terminal region provided outside the pixel region, the terminal region including connection terminals; and

a plurality of insulating layers provided from the pixel region to the terminal region continuously;

wherein:

the connection terminals each have a top surface and include at least a recessed portion, the recessed portion is recessed from the top surface toward the substrate;

in the pixel region, the plurality of insulating layers include a first inorganic insulating layer, an organic insulating layer provided on the first inorganic insulating layer, and a second inorganic insulating layer provided on the organic insulating layer;

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the first inorganic insulating layer and the organic insulating layer are provided in the recessed portion;

the pixel region and the terminal region are provided on a stack of the substrate and an underlying insulating layer provided on the substrate; and

the recessed portion is a portion where a part of the stack of the substrate and the underlying insulating layer is removed in a region for each of the connection terminals.

2. The display device according to claim 1, wherein the recessed portion is a portion where a part of each of the connection terminals is removed.

3. The display device according to claim 1, wherein the recessed portion is a portion where a part of the substrate is removed in a region for each of the connection terminals.

4. The display device according to claim 2, wherein the recessed portion is a portion where a part of the substrate is removed in a region for each of the connection terminals.

5. The display device according to claim 1, wherein the plurality of insulating layers cover the light emitting element.

6. The display device according to claim 1, wherein the at least a recessed portion comprises a plurality of recessed portions.

7. The display device according to claim 6, wherein the plurality of recessed portions are arranged in a direction.

8. The display device according to claim 6, wherein the plurality of recessed portions are arranged in a matrix.

9. The display device according to claim 6, wherein the plurality of recessed portions are arranged in a staggered array.

10. The display device according to claim 6, wherein the plurality of recessed portions include a first recessed portion and a second recessed portion which surrounds the first recessed portion.

11. The display device according to claim 1, wherein a part of the organic insulating layer is located above the top surface, and

the part of the organic insulating layer separates from and surrounds the recessed portion.

12. The display device according to claim 11, wherein a part of the first inorganic insulating layer is located on the top surface and in contact with the part of the organic insulating layer.

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专利名称(译)	显示装置的制造方法和显示装置		
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[标]申请(专利权)人(译)	株式会社日本显示器		
申请(专利权)人(译)	日本展示INC.		
当前申请(专利权)人(译)	日本展示INC.		
[标]发明人	KURIYAGAWA TAKESHI WATABE KAZUFUMI SATO TOSHIHIRO		
发明人	KURIYAGAWA, TAKESHI WATABE, KAZUFUMI SATO, TOSHIHIRO		
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摘要(译)

一种显示装置的制造方法，包括：像素区域，包括多个像素，每个像素包括发光元件和设置在像素区域外部并包括连接端子的端子区域；该方法包括：在每个连接端子的顶表面的一部分中形成凹进部分；在像素区域中依次形成第一无机绝缘层，有机绝缘层和第二无机绝缘层，并在端子区域中连续形成；在第一无机绝缘层和第二无机绝缘层直接堆叠的区域中蚀刻第一无机绝缘层和第二无机绝缘层，该区域在除了凹进部分之外的顶表面上。

